
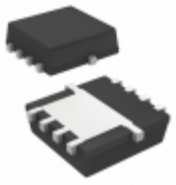
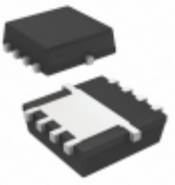


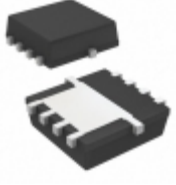



	<h2>SI7615DN-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI7615DN-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET P-CH 20V 35A 1212-8</p> <p>Datenblätter:  SI7615DN-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 28500 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI7615DN-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 20V 35A 1212-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	28500 pcs Stock
Hersteller Standard Vorlaufzeit	32 Weeks
detaillierte Beschreibung	P-Channel 20V 35A (Tc) 3.7W (Ta), 52W (Tc) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® 1212-8
Supplier Device-Gehäuse	PowerPAK® 1212-8
Verlustleistung (max)	3.7W (Ta), 52W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	35A (Tc)
Rds On (Max) @ Id, Vgs	3.9 mOhm @ 20A, 10V
VGS (th) (Max) @ Id	1.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	183nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	6000pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	6V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI7615DN-T1-GE3-ND

SI7615DN-T1-GE3 ist neu im Original, Suche SI7615DN-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7615DN-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7615DN-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI7619DN-T1-GE3 Vishay / Siliconix MOSFET P-CH 30V 24A 1212-8 PPAK</p>	 <p>SI7617DN-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 35A 1212-8 PPAK</p>	 <p>SI7617DN-T1-E3 Vishay Precision Group SI7617DN-T1-E3 VISHAY</p>	 <p>SI7615DN SI SI7615DN SI</p>
 <p>SI7617DN-T1-GE3 Vishay / Siliconix MOSFET P-CH 30V 35A 1212-8 PPAK</p>	 <p>SI7615DN-T1-E3 VISHAY SI7615DN-T1-E3 VISHAY</p>	 <p>SI7615DN-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 35A 1212-8</p>	 <p>SI7619DN-T1-E3 VISHAY VISHAY PAK1212</p>

heiße Teile

Mehr

 SI7485DP-T1-GE3	 SI7489DP	 SI7489DP-T1-GE3	 SI7489DP-T1-GE3	 SI7491DP
 SI7491DP-T1-GE3	 SI7491DP-T1-GE3	 SI7501DN-T1-E3	 SI7501DN-T1-E3	 SI7540ADP-T1-GE3
 SI7540ADP-T1-GE3	 SI7540DP-T1-E3	 SI7540DP-T1-E3	 SI7540DP-T1-GE3	 SI7540DP-T1-GE3
 SI7606DN-T1-E3	 SI7606DN-T1-GE3	 SI7611DN-T1-GE3	 SI7611DN-T1-GE3	 SI7613DN-T1-GE3
 SI7613DN-T1-GE3	 SI7615ADN-T1-GE3	 SI7615ADN-T1-GE3	 SI7615DN	 SI7615DN-T1-E3
 SI7615DN-T1-GE3	 SI7617DN-T1-GE3	 SI7617DN-T1-GE3	 SI7619DN-T1-GE3	 SI7619DN-T1-GE3
 SI7621DN-T1-GE3	 SI7621DN-T1-GE3	 SI7625DN-T1-GE3	 SI7625DN-T1-GE3	 SI7629DN-T1
 SI7629DN-T1-GE3	 SI7629DN-T1-GE3	 SI7633DP-T1-GE3	 SI7633DP-T1-GE3	 SI7634BDP
 SI7634BDP-T1-E3	 SI7634BDP-T1-E3	 SI7634BDP-T1-GE3	 SI7634BDP-T1-GE3	 SI7634DP-T1-E3
 SI7634DP-T1-GE3	 SI7635DP	 SI7635DP-T1-GE3	 SI7635DP-T1-GE3	 SI7636DP

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